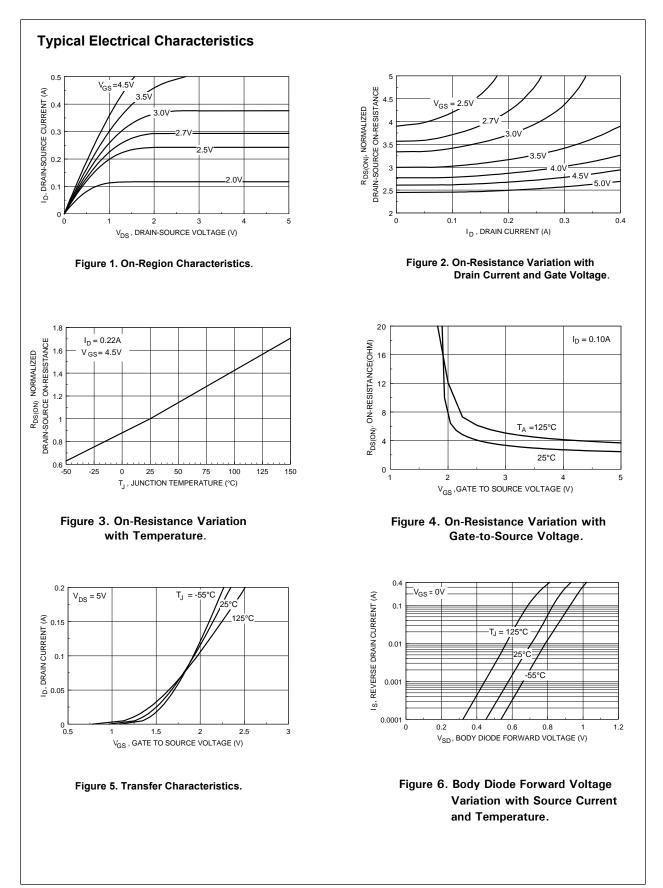
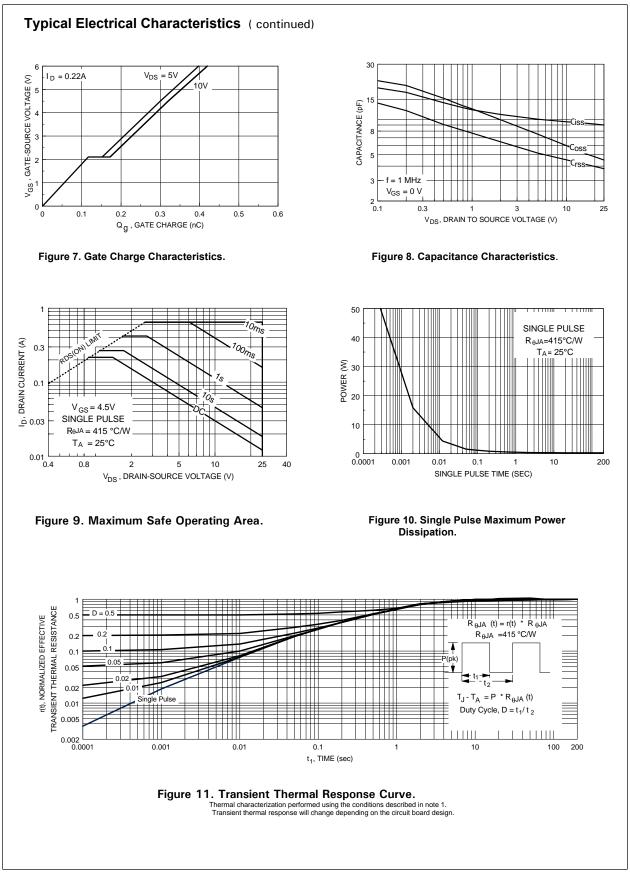
	IRCHILD				July 1999
-	6301N N-Channel, Digital	FET			
General Description These dual N-Channel logic level enhancement mode field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. This device has been designed especially for low voltage applications as a replacement for bipolar digital transistors and small signal MOSFETs.			 Features 25 V, 0.22 A continuous, 0.65 A peak. R_{DS(ON)} = 4 Ω @ V_{GS} = 4.5 V, R_{DS(ON)} = 5 Ω @ V_{GS} = 2.7 V. Very low level gate drive requirements allowing direct operation in 3 V circuits (V_{GS(th)} < 1.5 V). Gate-Source Zener for ESD ruggedness (>6kV Human Body Model). Compact industry standard SC70-6 surface mount package. 		
(÷	8.88 199			
SC7	0-6 SOT-23	SuperSOT [™] -6	SuperSOT [™] -8	SO-8	SOT-223
	D1 S2	D2 G1	L	or 4 *	6 or 3
Units in: Absol	G2 D1 SC70-6 SC70-6 SC70-6 SC70-6	G1 1 nterchangeable. ion and will not affect the fu	2 nctionality of the device.		5 or 2 4 or 1 *
Units ins Absol Symbol	G2 D1 OUTS are symmetrical; pin 1 and 4 are i side the carrier can be of either orientat ute Maximum Ratings Parameter	G1 1 nterchangeable. ion and will not affect the fu	2 nctionality of the device.	TOT 5 3 or 6 3 or 6	5 or 2 4 or 1 *
	outs are symmetrical; pin 1 and 4 are i side the carrier can be of either orientat ute Maximum Ratings Parameter Drain-Source Voltage	G1 1 nterchangeable. ion and will not affect the fu	2 nctionality of the device.	TDG6301N 25	5 or 2 4 or 1 *
Units in: Absol Symbol / _{DSS} / _{GSS}	outs are symmetrical; pin 1 and 4 are i side the carrier can be of either orientat ute Maximum Ratings Parameter Drain-Source Voltage Gate-Source Voltage	$G1^{-1}$	2 nctionality of the device.	TOT 5 3 or 6 3 or 6	5 or 2 4 or 1 *
Units ins	G2 D1 G2 D1 G2 SC70-6 SC70-7	$G1^{-1}$	2 nctionality of the device.	EDG6301N 25 8 0.22	5 or 2 4 or 1 * Units V V
Units in: Absol Symbol /DSS /GSS D D	outs are symmetrical; pin 1 and 4 are i side the carrier can be of either orientat ute Maximum Ratings Parameter Drain-Source Voltage Gate-Source Voltage Drain/Output Current - Cor - Pute	$G1^{T}$ nterchangeable. ion and will not affect the fut $T_A = 25^{\circ}C \text{ unless otherw}$ ntinuous sed (Note 1)	ctionality of the device.	TOT 5 3 or 6 3 or 6 5 OF 6	5 or 2 4 or 1 * Units V V A
Units ins Absol Symbol Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss	G2 D1 SC70-6 SC70-7 SC70-7	G1 I I I I I I I I I I I I I I I I I I I	ctionality of the device.	EDG6301N 25 8 0.22 0.65 0.3	5 or 2 4 or 1 * V V V V W
Units in: Absol Symbol V _{DSS} V _{GSS} b C C C C C C C C C C C C C	G2 D1 G2 S D1 G2 S S SC70-6 S S S outs are symmetrical; pin 1 and 4 are i S S S outs are symmetrical; pin 1 and 4 are i S S S ute Maximum Ratings Parameter Drain-Source Voltage Gate-Source Voltage Drain/Output Current - Cor - Puls Maximum Power Dissipation Operating and Storage Temper Electrostatic Discharge Rating S	G1 I I I I I I I I I I I I I I I I I I I	ctionality of the device.	Tor 5 Bor 6 Bor 6 Bor 6 Bor 6 Cor 5 0.22 0.65 0.3 -55 to 150	5 or 2 4 or 1 * V V V A W °C

Symbol	Parameter	Conditions	Min	Тур	Max	Units
OFF CHAR	ACTERISTICS					•
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_{D} = 250 \mu A$	25			V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient	$I_{\rm D}$ = 250 µA, Referenced to 25 °C		25		mV /°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 20 V, V_{GS} = 0 V$			1	μA
		$T_{J} = 55^{\circ}C$			10	μA
I _{GSS}	Gate - Body Leakage Current	$V_{GS} = 8 V, V_{DS} = 0 V$			100	nA
ON CHARA	CTERISTICS (Note 2)			1	1	
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.65	0.85	1.5	V
$\Delta V_{GS(th)} / \Delta T_{J}$	Gate Threshold Voltage Temp.Coefficient	$I_{\rm D}$ = 250 µA, Referenced to 25 °C		-2.1		mV /°C
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 4.5 \text{ V}, I_{D} = 0.22 \text{ A}$		2.6	4	Ω
		T _J =125°C		5.3	7	
		$V_{GS} = 2.7 \text{ V}, I_{D} = 0.19 \text{ A}$		3.7	5	
I _{D(ON)}	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$	0.22			А
9 _{FS}	Forward Transconductance	$V_{DS} = 5 V, I_{D} = 0.22 A$		0.2		S
DYNAMIC C	HARACTERISTICS					
C _{iss}	Input Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		9.5		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		6		pF
C _{rss}	Reverse Transfer Capacitance			1.3		pF
SWITCHING	CHARACTERISTICS (Note 2)					
t _{D(on)}	Tum - On Delay Time	$V_{DD} = 5 V, I_{D} = 0.5 A,$		5	10	ns
Ļ	Turn - On Rise Time	$V_{GS} = 4.5 \text{ V}, \text{ R}_{GEN} = 50 \Omega$		4.5	10	ns
t _{D(off)}	Turn - Off Delay Time			4	8	ns
t _r	Turn - Off Fall Time			3.2	7	ns
Q _g	Total Gate Charge	$V_{DS} = 5 V, I_D = 0.22 A,$		0.29	0.4	nC
Q _{gs}	Gate-Source Charge	$V_{GS}^{00} = 4.5 V$		0.12		nC
Q _{gd}	Gate-Drain Charge	Charge		0.03		nC
DRAIN-SOU	RCE DIODE CHARACTERISTICS AND MAXIM	UM RATINGS				
l _s	Maximum Continuous Source Current				0.25	A
V _{SD}	Drain-Source Diode Forward Voltage	$V_{\rm GS} = 0 \ V, \ I_{\rm S} = 0.25 \ A \ ({\rm Note} \ 2)$		0.8	1.2	V

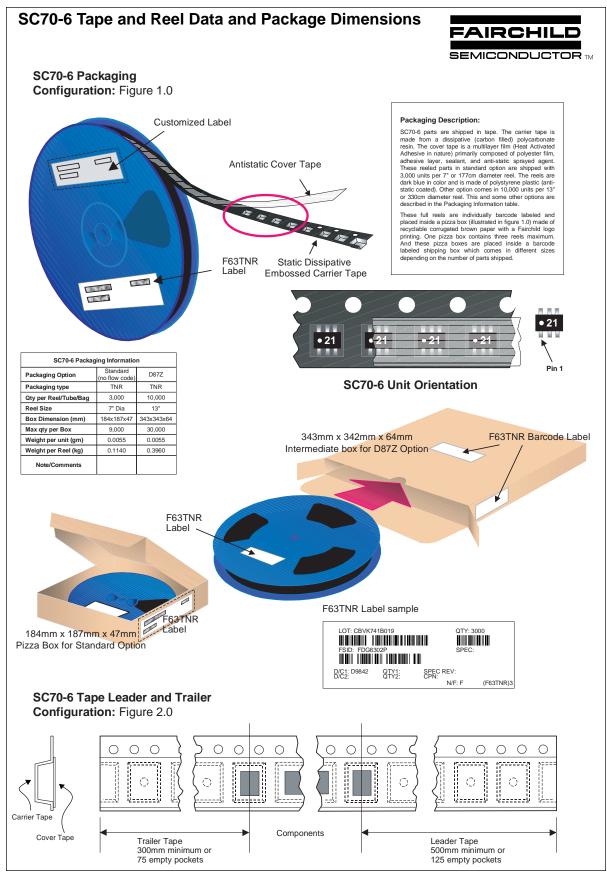
Notes:

1. R_{pk} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{pk} is guaranteed y design while $R_{y_{0}A}$ is determined by the user's board design. $R_{y_{0}A} = 415^{\circ}$ C/W on minimum pad mounting on FR-4 board in still air. 2. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2.0%.

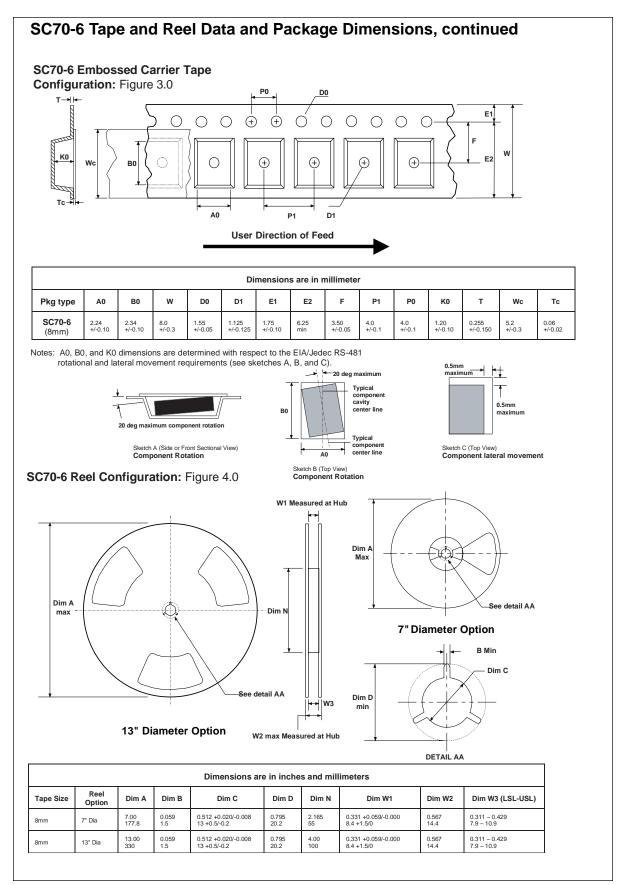


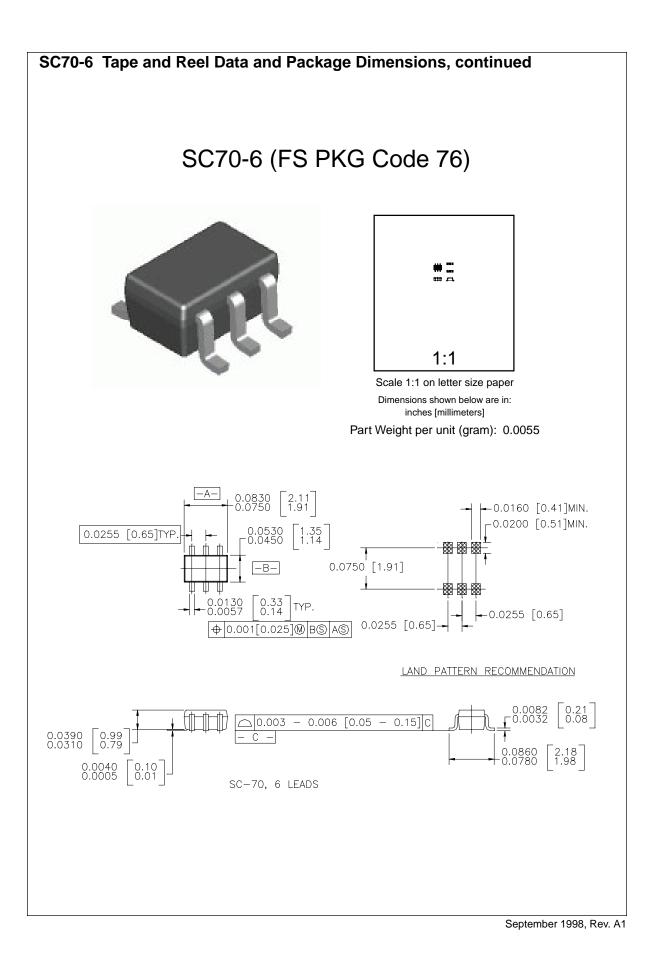


FDG6301N Rev.E1



August 1999, Rev. C





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